

ABSTRACT OF THE DISCLOSURE

Methods and devices are disclosed utilizing a ~~phosphorous-doped~~phosphorous-doped oxide layer that is added prior to re-oxidation. This allows greater control of the re-oxidation process and greater control of the performance characteristics of semiconductor devices such as flash memory. For flash memory, greater control is gained over programming rates, erase rates, data retention and ~~self-aligned~~self-aligned source resistance.

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